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## **Design and Fabrication of High Efficiency Phosphorescent OLEDs**

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In this work, the power efficiency of organic light emitting diodes (OLEDs) was improved by increasing the internal quantum efficiency, reducing the drive voltage and enhancing of the optical out-coupling efficiency. High quantum efficiency was achieved by using fac-tris(2-phenylpyridine) iridium complex ( $Ir(ppy)_3$ ) and wide-energy-gap materials with high triplet energies. The organic layers at the electrode interfaces were chemically doped, *p*-type and *n*-type, to reduce operating voltage. Furthermore, we optimized the optical interference effect by using various thicknesses of the *n*-doped layer with high conductivity. The optimized device exhibited green emission peaking at approximately 510 nm, and the external quantum efficiency (EQE) of 24.5% (88 cd/A). A high power efficiency of 90 lm/W was observed at 100 cd/m<sup>2</sup> (3.05 V).